EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1263	326/80,81.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:40
L2	0	326/80,81.ccls. same cmos same saturation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:41
L3	6	326/80,81.ccls. and cmos same saturation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:44
L4	93	326/80,81.ccls. and cmos same diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:45
L5	57	326/80,81.ccls. and cmos same diode same output	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:45
L6	15	326/80,81.ccls. and cmos same diode same output near4 (stage node)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:52
L7	1	"7046036".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 11:53
L8	2	("6201428" | "6388475").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 11:55
L9	3	("6201428").URPN.	USPAT	OR	ON	2006/05/20 11:56

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L10	6	("6388475").URPN.	USPAT	OR	ON	2006/05/20 11:57
L11	2	("6201428" | "6388475"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 11:59
L12	1737	cmos same ttl same level	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:00
L13	1131451	cmos same ttl same levelnear2 shift$3	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:00
L14	178	cmos same ttl same level near2 shift$3	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:01
L15	1	cmos same ttl same level near2 shift$3 same core	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:01
L16	9	cmos same ttl same level near2 shift$3 and gate near3 diode	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:04
L17	91	cmos same ttl same level near2 shift$3 and bias$4	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:04
L18	14	cmos same ttl same level near2 shift$3 same bias$4	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:07
L19	2	cmos same ttl same level near2 shift$3 same bias$4 same diode	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:09
L20	32	cmos same level near2 shift$3 same bias$4 same diode	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:10
L21	3	cmos same level near2 shift$3 same bias$4 same diode and protection	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:11
L22	0	cmos same level near2 shift$3 same bias$4 same diode with gate and protection	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:11
L23	7	cmos same level near2 shift$3 same bias$4 same diode with gate	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:27
L24	1	cmos same level near2 shift$3 same bias$4 same diode near2 gate	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/20 12:27
L29	27	relatively adj high adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 12:54

L30	1	relatively adj high adj voltage and relatively adj low adj voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 12:52
L31	1	relatively adj high near voltage and relatively adj low near voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 12:52
L32	0	relatively adj high near voltage and relatively adj low near voltage	US-PGPUB	OR	ON	2006/05/20 12:53
L33	0	relatively adj high near voltage and "20050146819"	US-PGPUB	OR	ON	2006/05/20 12:53
L34	0	relatively near high near voltage and "20050146819"	US-PGPUB	OR	ON	2006/05/20 12:53
L35	1	"20050146819"	US-PGPUB	OR	ON	2006/05/20 12:54
L36	0	"20050146819" and "relatively low voltage"	US-PGPUB	OR	ON	2006/05/20 12:54
L37	32	relatively adj low adj voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:00
L38	1	37 and 29	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 12:56
L39	54	relatively near2 low near2 voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:00
L40	45	relatively near2 high near2 voltage	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:01

L41	5	39 and 40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:00
L42	0	(relatively near2 high near2 voltage).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:01
L43	0	(relatively near2 low near2 voltage).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:01
L44	0	(relatively with low with voltage).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/20 13:01
S1	2	"20050146819"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 16:26
S2	79	esd and input adj stage same output adj stage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 12:07
S3	0	esd and input adj stage same output adj stage same doides	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:08
S4	2	esd and input adj stage same output adj stage same diodes	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:10

S5	43	esd and output adj stage same diodes	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:12
S6	0	esd and output adj stage same diodes same vow adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:13
S7	1	esd and output adj stage same diodes same low adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:13
S8	26	esd and output adj stage same diodes and low adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:13
S9	5	esd and output adj stage same diodes and low adj voltage and high adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 12:22
S10	2	esd and output adj stage same diodes same cmos and low adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 13:56
S11	2	esd and output adj stage same diodes same gate same cmos and low adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 14:09
S12	14	esd and output adj stage and low adj voltage and high adj voltage and intermediate adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 14:12

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S13	91	esd and output adj stage and output with diode with gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 14:13
S14	3	esd same output adj stage and output with diode with gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 14:42
S15	19	protection same output adj stage and output and vcc and vdd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/16 14:44
S16	14	protection same output adj stage and output same diode and vcc and vdd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:46
S17	201	output adj stage and output same diode and vcc and vdd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:46
S18	176	output adj stage and output same diode and vcc and vdd and source and drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:47
S19	137	output adj stage and output same diode same source and drain and vcc and vdd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:52
S20	1	output adj stage and output same diode same source and drain and vcc and vdd and vdd1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:48

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S21	1	output adj stage and output same diode same source and drain and vcc and vdd2 and vdd1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:49
S22	2	"5440244".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:49
S23	1	"5440244".pn. and diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:50
S24	132	output adj stage and output same diode same source same drain same (cmos)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:52
S25	425	output adj stage and output same diode same source same drain same (cmos mos)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 15:24
S26	44	output adj stage and output same diode same source same drain same (cmos mos) same protect$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:54
S27	20	output adj stage same output same diode same source same drain same (cmos mos) same protect$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 14:54
S28	3	output adj stage same output same diode near2 gate same source same drain same (cmos mos) same protect$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 15:04

S29	2	"5867010".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 15:06
S30	2	"5844425".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 15:06
S31	129	output adj stage and output same diode same source same drain same (cmos mos) and transient	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 15:28
S32	3	output adj stage and output same diode same source same drain same (cmos mos) and transient and 361/56.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 15:29
S33	8	output adj stage and output same diode same source same drain same (cmos mos) and 361/56.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 16:09
S34	1	kirhoff	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 16:12
S35	3259	kirchhoff	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/16 16:12
S36	52760	output adj stage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 16:27

S37	7586	S36 same diode	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 16:27
S38	405	S37 same protection	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 16:28
S39	14	S38 same cmos	US-PGPUB ; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 16:28